

PHASE CONTROL THYRISTORS

- **Junction Size:** Square 185 mils
- **Wafer Size:** 4"
- **V_{RRM} Class:** 800 V
- **Passivation Process:** Glassivated MESA
- **Reference IR Packaged Part:** 25TTS Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V _{TM} Maximum On-state Voltage	1.25 V	T _J = 25°C, I _T = 16 A
V _{RRM} Reverse Breakdown Voltage	800 V	T _J = 25°C, I _{RRM} = 100 µA (1)
I _{GT} Max. Required DC Gate Current to Trigger	60 mA	T _J = 25°C, anode supply = 6 V, resistive load
V _{GT} Max. Required DC Gate Voltage to Trigger	2 V	T _J = 25°C, anode supply = 6 V, resistive load
I _H Holding Current Range	5 to 100 mA	Anode supply = 6 V, resistive load
I _L Maximum Latching Current	200 mA	Anode supply = 6 V, resistive load

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 µm)
Chip Dimensions	185 x 185 mils (see drawing)
Wafer Diameter	100 mm, with std. <110> flat
Wafer Thickness	350 µm ± 10 µm
Maximum Width of Sawing Line	130 µm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR185BG08DCB

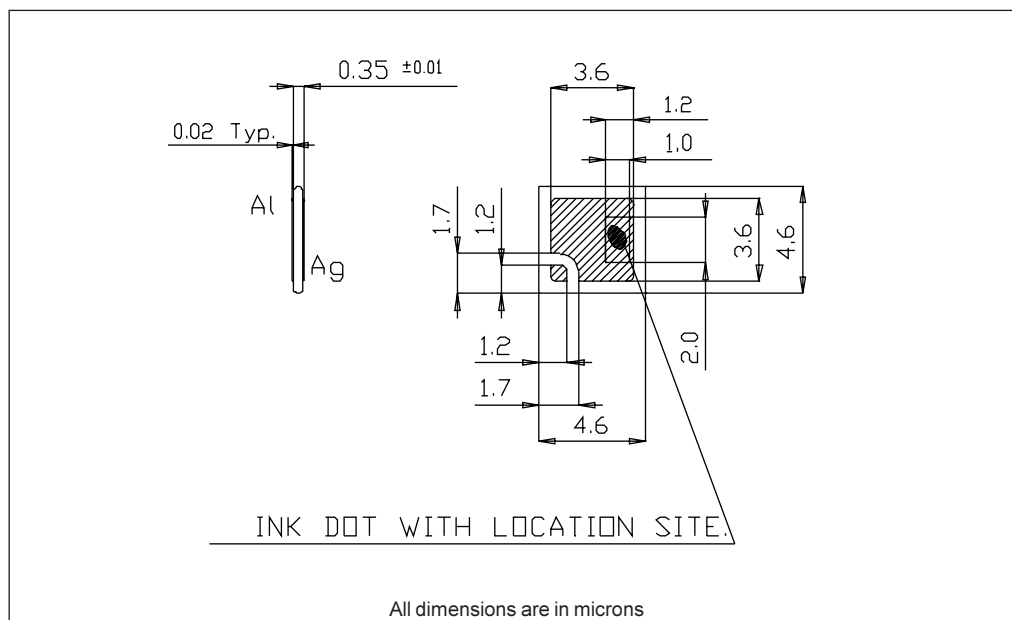
Bulletin I0209J rev. A 09/99

International
IR Rectifier

Ordering Information Table

Device Code						
IR	185	B	G	08	D	CB
①	②	③	④	⑤	⑥	⑦
1	- International Rectifier Device					
2	- Chip Dimension in Mils					
3	- Type of Device: B = Wire Bondable SCR					
4	- Passivation Process: G = Glassivated MESA					
5	- Voltage code: Code x 100 = V_{RRM}					
6	- Metallization: D = Silver (Anode) - Aluminium (Cathode)					
7	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier					

Outline Table



Wafer Layout

